

dielectric layer, and claim 9 has been amended to replace "or" with --and--. As a result, claims 3, 4, 9, 11-16 and 21 are all allowable with respect to 35 U.S.C. § 112, second paragraph.

The Examiner has rejected claims 20-23 under 35 U.S.C. § 112, first paragraph. Applicant respectfully traverses this rejection, however, to expedite prosecution has amended claims 20 and 21 to render this rejection moot.

The Examiner has indicated that claim 2 will be allowable if rewritten in independent form including all the limitations of the base claim (claim 1) and any intervening claims (none). Applicant has so amended claim 2 and hence claim 2 is now in condition for allowance. Claims 3-5, and 8-16 all depend from claim 2 and are allowable for at least depending from an allowable independent claim.

The Examiner has indicated that claim 6 will be allowable if rewritten in independent form to include all the limitations of the base claim (claim 1) and any intervening claims (none). Applicant has so amended claim 6 and claim 6 is now in condition for allowance. Claim 7 depends from claim 6 and is allowable for at least depending from an allowable independent claim.

As amended, independent claim 20 provides a method of forming a semiconductor integrated circuit. The method includes, *inter alia*, selectively implanting halogen-containing impurities through the gate dielectric layer and into the second region. The method further includes simultaneously forming a first thickness of dielectric material overlying the first region and a second thickness of dielectric material overlying the second region by an oxidizing process. In contrast to claim 20, Takagi fails to disclose, teach or suggest such a method. For example, as recognized by the Examiner, Takagi fails to disclose, teach or suggest the particular ion or impurities implanted into the semiconductor substrate to subsequently form dielectric materials of desired thickness. Additionally, the implantation step in Takagi is directed into a semiconductor substrate. In contrast, claim 20 requires that the implantation of halogen-containing impurities occur through the gate dielectric layer. Hence for at least these reasons, claim 20 is allowable over the cited art. Claims 22 and 23 depend from claim 20 and are allowable for at least depending from an allowable independent claim.

The Examiner has indicated that claim 21 will be allowable if rewritten to overcome the 35 U.S.C. § 112, second paragraph rejection, and to include all the limitations of

the base claim (claim 20). Claim 21 has been so amended and is now in condition for allowance.


Added claims 24-28 are directed to additional novel features of the invention and are similarly allowable. For example, claim 24 is similar to claim 23 rewritten in independent form, and independent claim 27 is similar to claim 9 rewritten in independent form. Applicant contends that added claims 24-28 are all in condition for allowance, and do not add new matter.

CONCLUSION

In view of the foregoing, Applicants believe all claims now pending in this Application are in condition for allowance. The issuance of a formal Notice of Allowance at an early date is respectfully requested.

If the Examiner believes a telephone conference would expedite prosecution of this application, please telephone the undersigned at 303-571-4000.

Respectfully submitted,



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